

Correction to MoS₂ Field-Effect Transistor for Next-Generation Label-Free

Biosensors [ACS Nano 2014, 8, 3992–4003.

DOI: 10.1021/nn5009148]. Deblina Sarkar,* Wei Liu, Xuejun Xie, Aaron C. Anselmo, Samir Mitragotri, and Kaustav Banerjee*

1. On the eighth page of the Supporting Information, eq s2 is misrepresented. It should be written

$$\lambda_{\text{SOI}} = \sqrt{\frac{\epsilon_s}{\epsilon_d} t_d t_s} \quad (\text{s2})$$

with the value of λ on the fourth line of the text below corrected to $\lambda = L_g/5$.

2. On the 9th and 10th lines of the text below equation s4, on the ninth page of the Supporting Information, the sentence "Thus, with a decrease in barrier, current will increase following the trend $I \propto e^{E/k_B T}$." should be restated:

"Thus, with a decrease in barrier (say by ΔE), current will increase following the trend $\Delta I_d \propto e^{\Delta E/k_B T}$.", to be more precise.

These changes rectify simple typographical errors (or provide clarifications), and no calculations or analyses in the paper or in the Supporting Information are affected by these changes.

Published online May 02, 2014
10.1021/nn502216d